RGP02-12E THRU RGP02-20E

GLASS PASSIVATED JUNCTION FAST SWITCHING RECTIFIER Forward Current - 0.5 Ampere

Reverse Voltage - 1200 to 2000 Volts

FEATURES

CASE STYLE GP10E .0 (25.4) 0.160 (4 1.0 (25.4

Dimensions in inches and (millimeters) * Glass-plastic encapsulation technique is covered by Patent No. 3,996,602 and brazed-lead assembly by Patent No. 3,930,306

- Plastic package has **Underwriters Laboratory** Flammability Classification 94V-0
- High temperature metallurgically bonded construction
- Capable of meeting environmental standards of MIL-S-19500
- For use in high frequency rectifier circuits
- Fast switching for high efficiency
- Glass passivated cavity-free junctions
- ♦ 0.5 Ampere operation at TA=55°C with no thermal runaway
- Typical IR less than 0.2µA
- High temperature soldering guaranteed: 350°C/10 seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: Molded plastic over glass body Terminals: Plated axial leads, solderable per MIL-STD-750 Method 2026 Polarity: Color band denotes cathode end

Mounting Position: Any Weight: 0.012 ounce, 0.3 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.							
WW 100	SYMBOLS	RGP02 -12E	RGP02 -14E	RGP02 -16E	RGP02 -18E	RGP02 -20E	UNITS
Maximum repetitive peak reverse voltage	VRRM	1200	1400	1600	1800	2000	Volts
Maximum RMS voltage	VRMS	840	980	1120	1260	1400	Volts
Maximum DC blocking voltage	VDC	1200	1400	1600	1800	2000	Volts
Maximum average forward rectified current 0.375" (9.5mm) lead length at TA=55°C	l(AV)	NT.N	N	0.5	DOX.COM	MTW	Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	M.TW		20.0	100X.C	OM.TY	Amps
Maximum instantaneous forward voltage at 0.1A	VF	T.Mo	1.8				
Maximum DC reverse currentTA=25°Cat rated DC blocking voltageTA=125°C	IR	5.0 50.0					μA
Maximum reverse recovery time (NOTE 1)	trr	300.0					ns
Typical junction capacitance (NOTE 2)	CJ	5.0					pF
Typical thermal resistance (NOTE 3)	Roja Rojl	65.0 30.0					°C/W
Operating junction and storage temperature range	TJ, TSTG	-65 <u>to +175</u>					°C

NOTES:

(1) Reverse recovery test conditions: IF=0.5A, IR=1.0A, Irr=0.25A

(2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts

(3) Thermal resistance from junction to ambient and from junction to lead at 0.375" (9.5mm) lead length, P.C.B. mounted

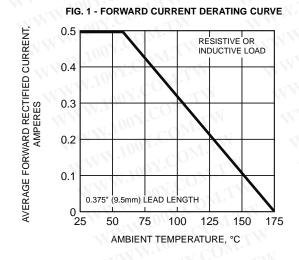
特力材料 886-3-5753170 胜特力电子(上海) 86-21-54151736

胜特力电子(深圳) 86-755-83298787

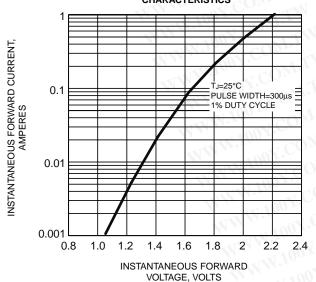
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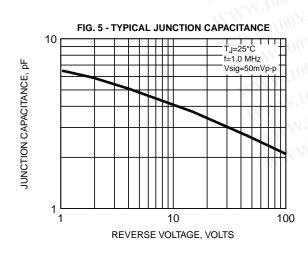
SEMICONDUCTOR

RATINGS AND CHARACTERISTIC CURVES RGP02-12E THRU RGP02-20E









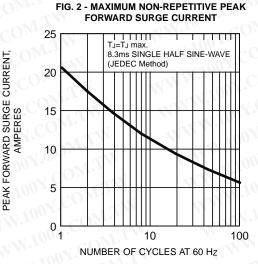
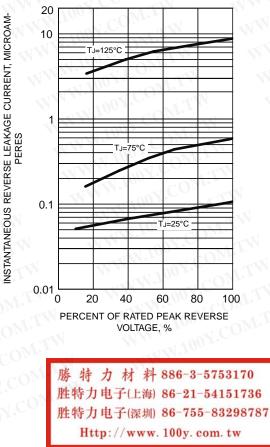


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS



GENERAL SEMICONDUCTOR[®]